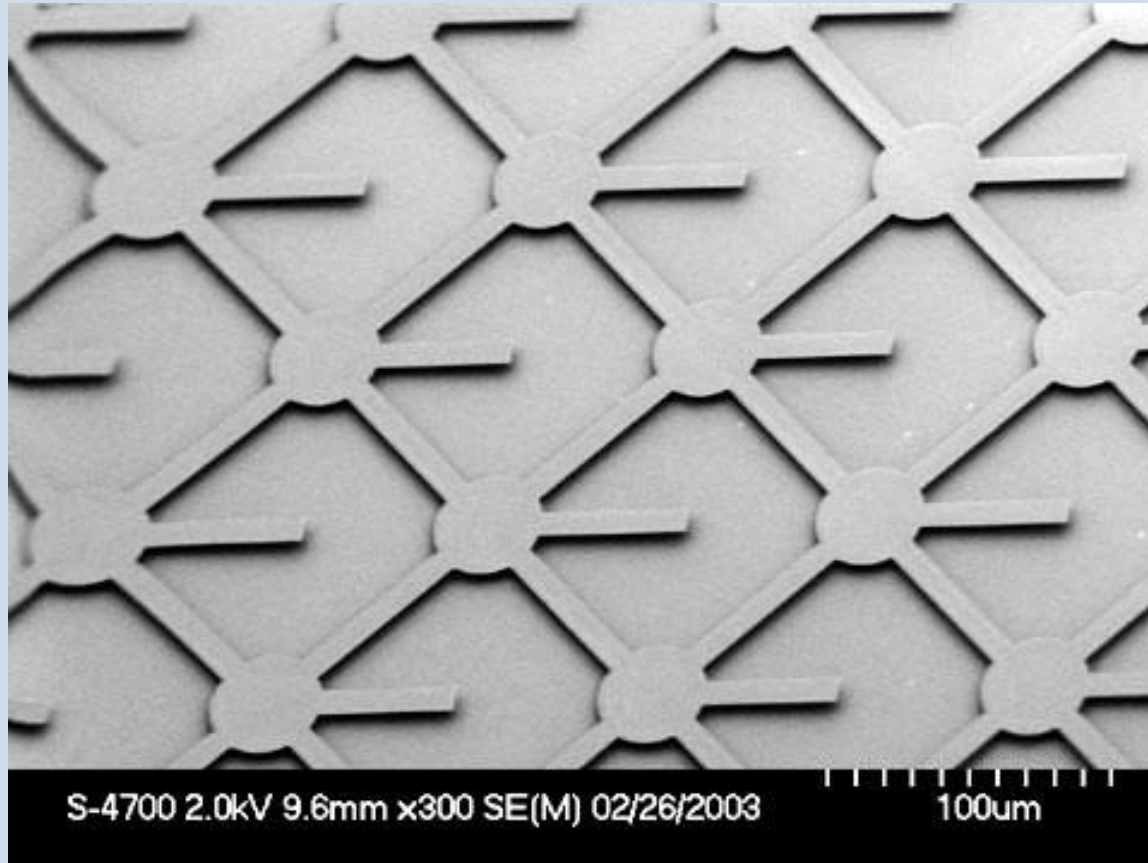


MEMS Process

Examples using

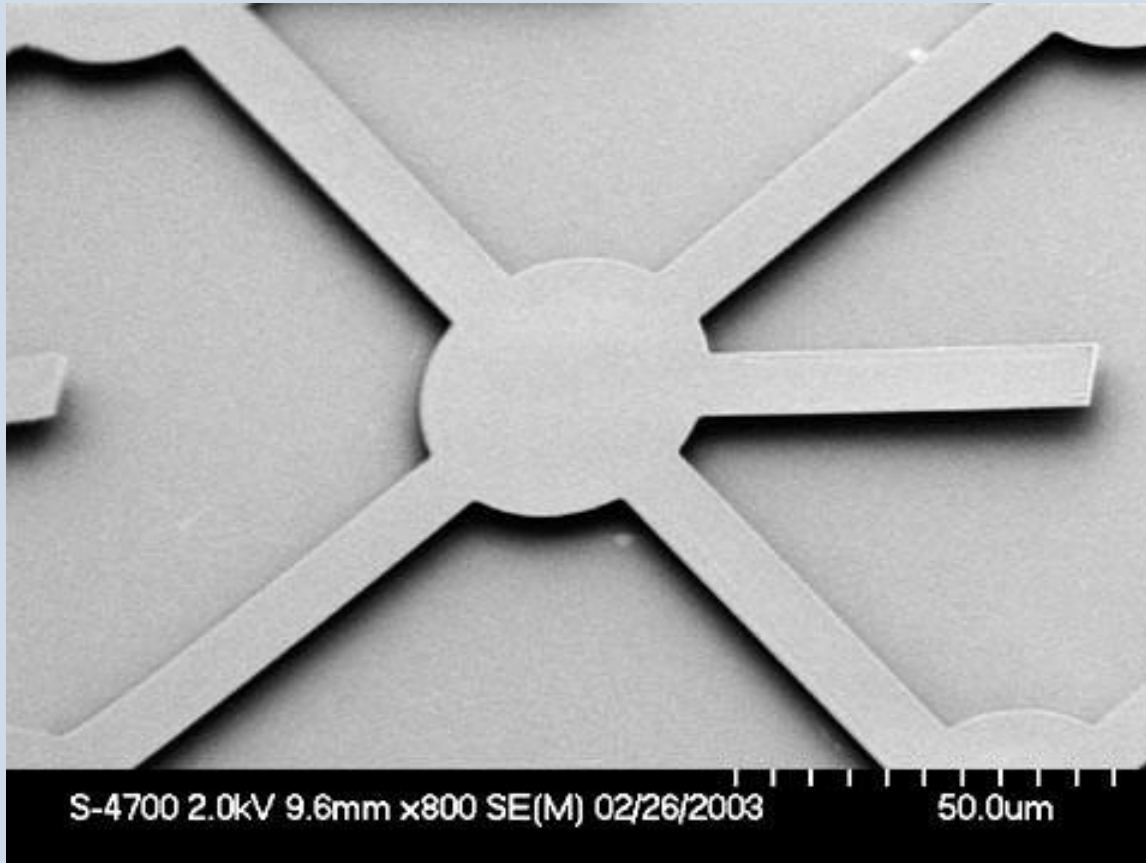
tousimis[®] CPD Process

***SEM View of Coupled Oscillators Made of
Low Stress Silicon Nitride. 300x***



Cornell Nanoscale Facility and Department of Applied Physics, USA
Rob Ilic and H.G. Craighead (Craighead Group)

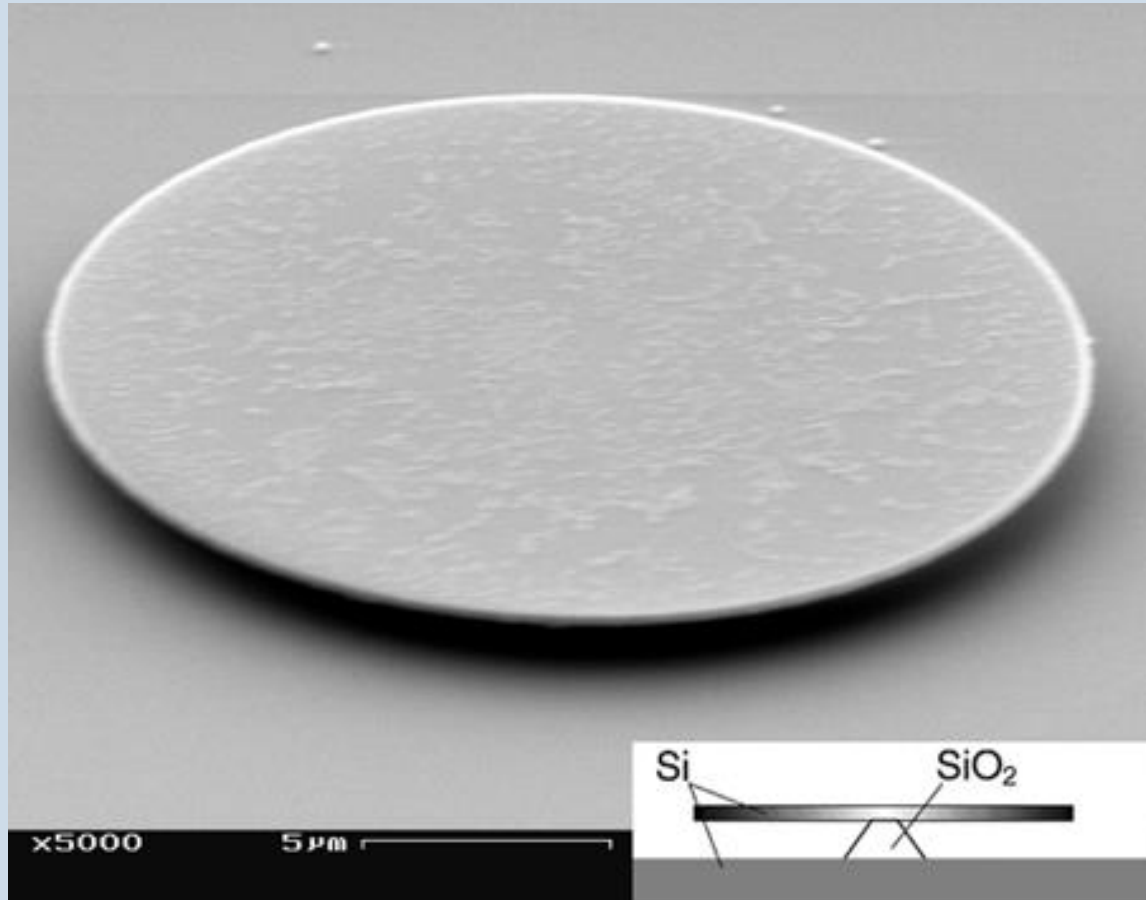
Single Coupled Oscillator Made Out of Low Stress Silicon Nitride. Mag = 800x



***1 μ m distance
between silicon
substrate and
device***

Cornell Nanoscale Facility and Department of Applied Physics, USA
Rob Ilic and H.G. Craighead (Craighead Group)

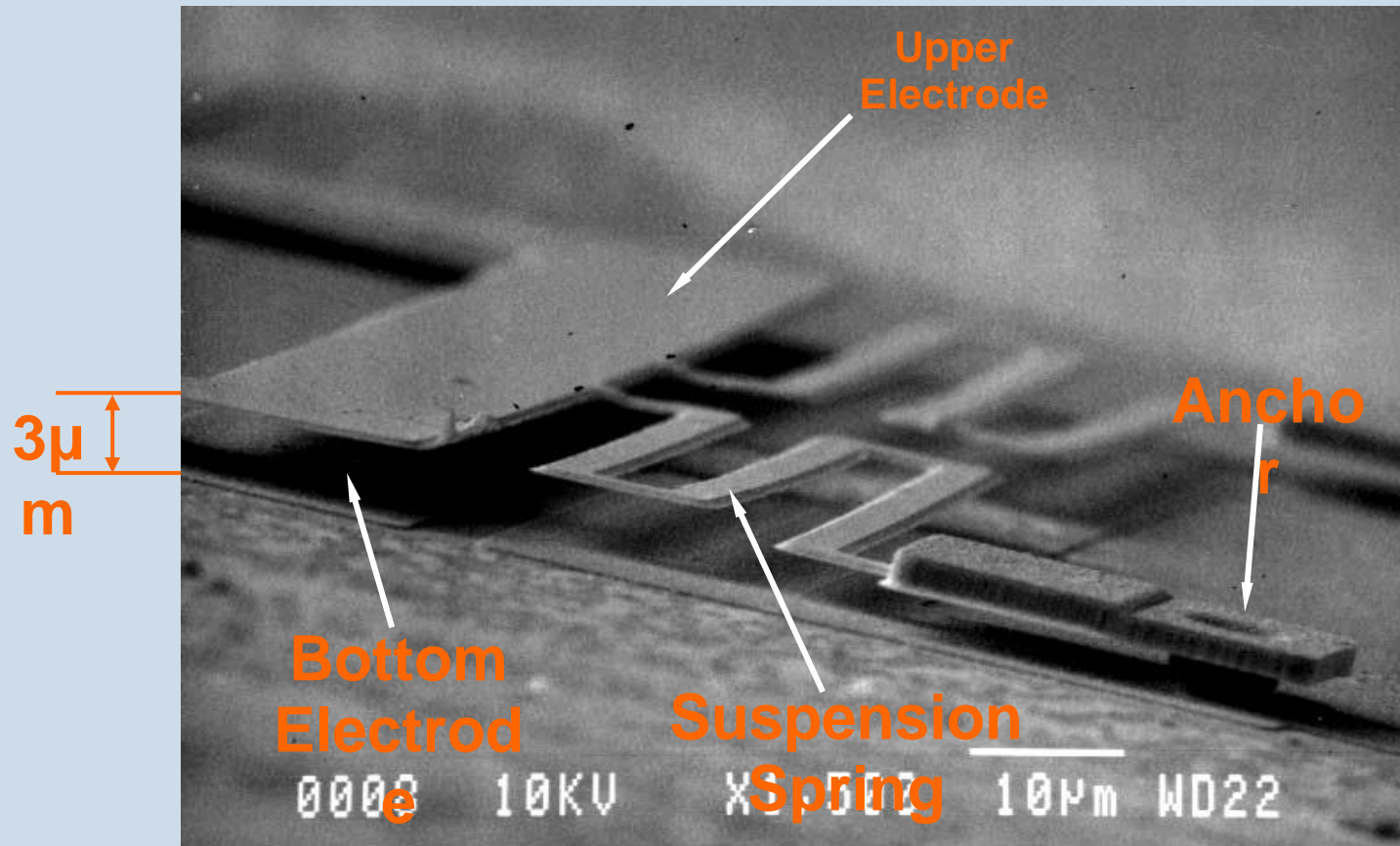
MEMS Based Resonant Device



*250nm Si Thickness
1 μm Gap from
Si Substrate
~20 μm in Diameter*

Cornell Nanoscale Facility and Department of Applied Physics, USA
Rob Ilic and H.G. Craighead (Craighead Group)

Tiltable Microplatform



University of Michigan at Ann Arbor, Dept. of Engineering, USA

Yuan Xie, Ph.D.

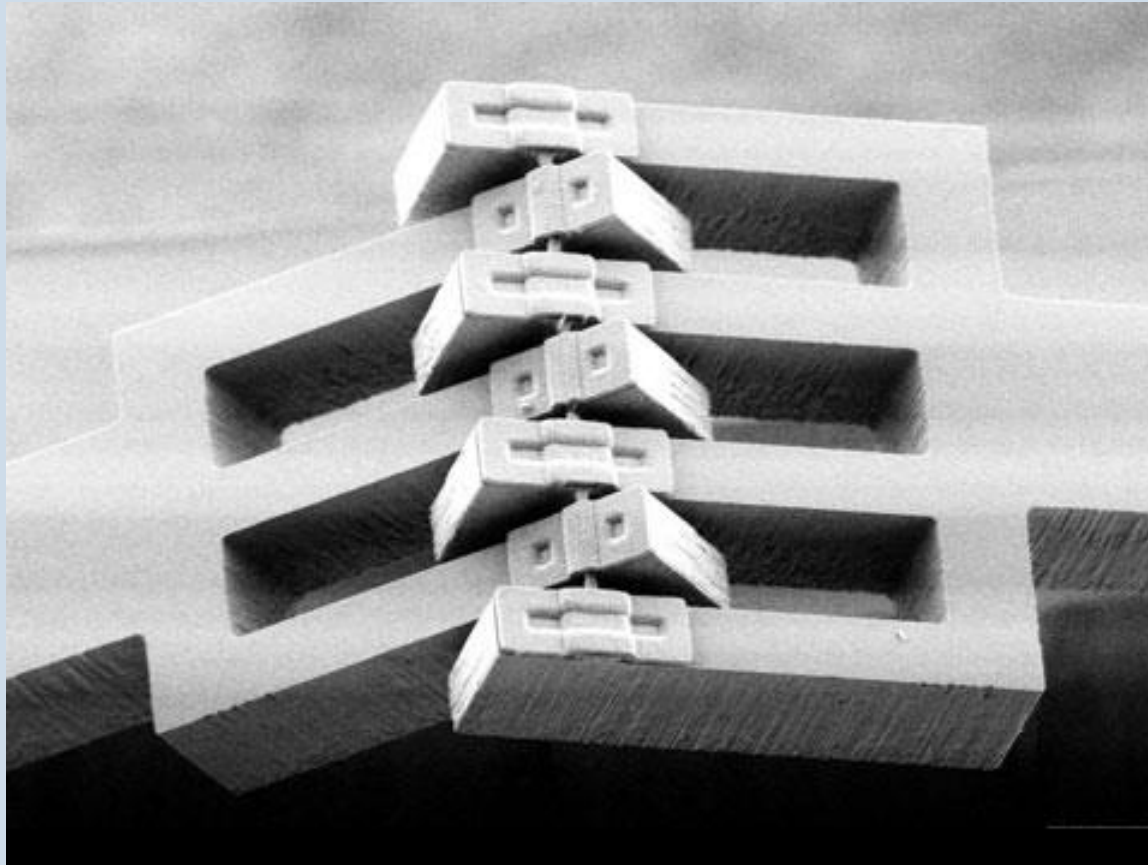
Silicon MicroRobots



University of California at Berkeley & Micropropulsion Corp. USA

Seth Hollar and Anita Flynn

Silicon MicroRobots - Elbow hinge - full view

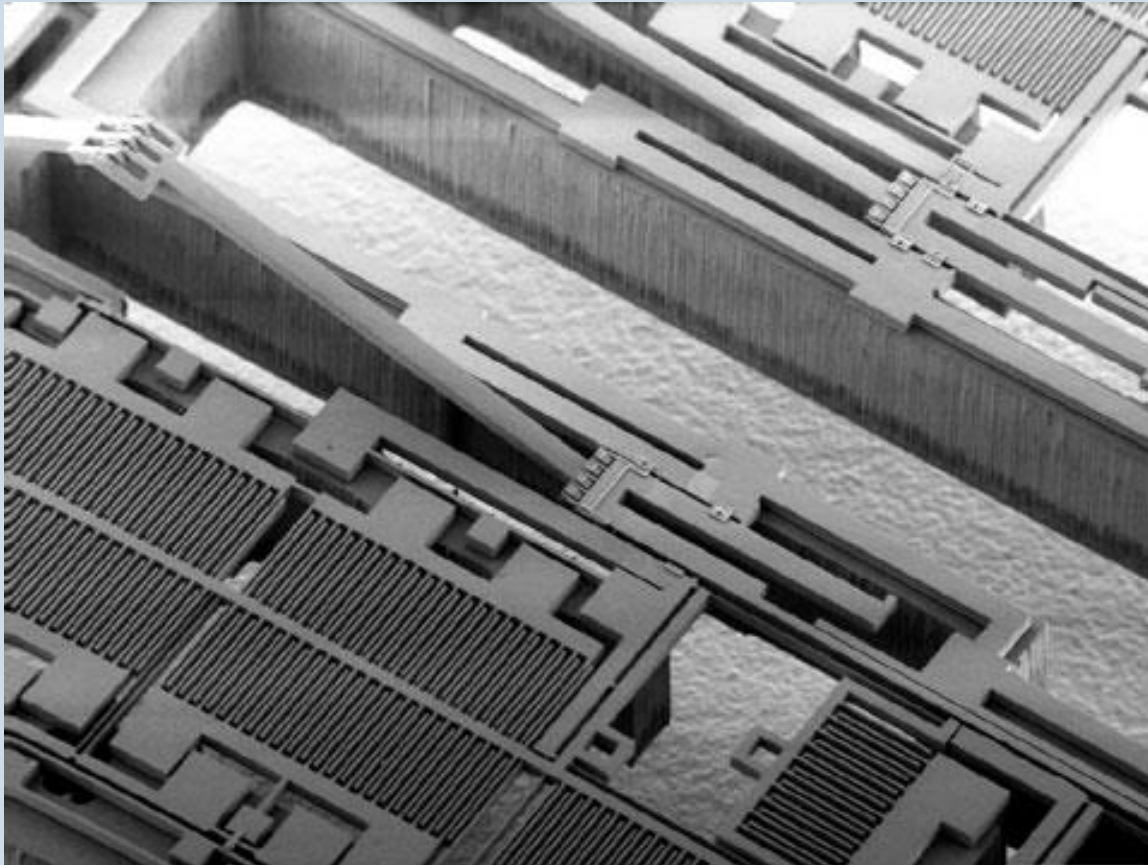


University of California at Berkeley & Micropropulsion Corp. USA

Seth Hollar and Anita Flynn

Silicon Microrobots

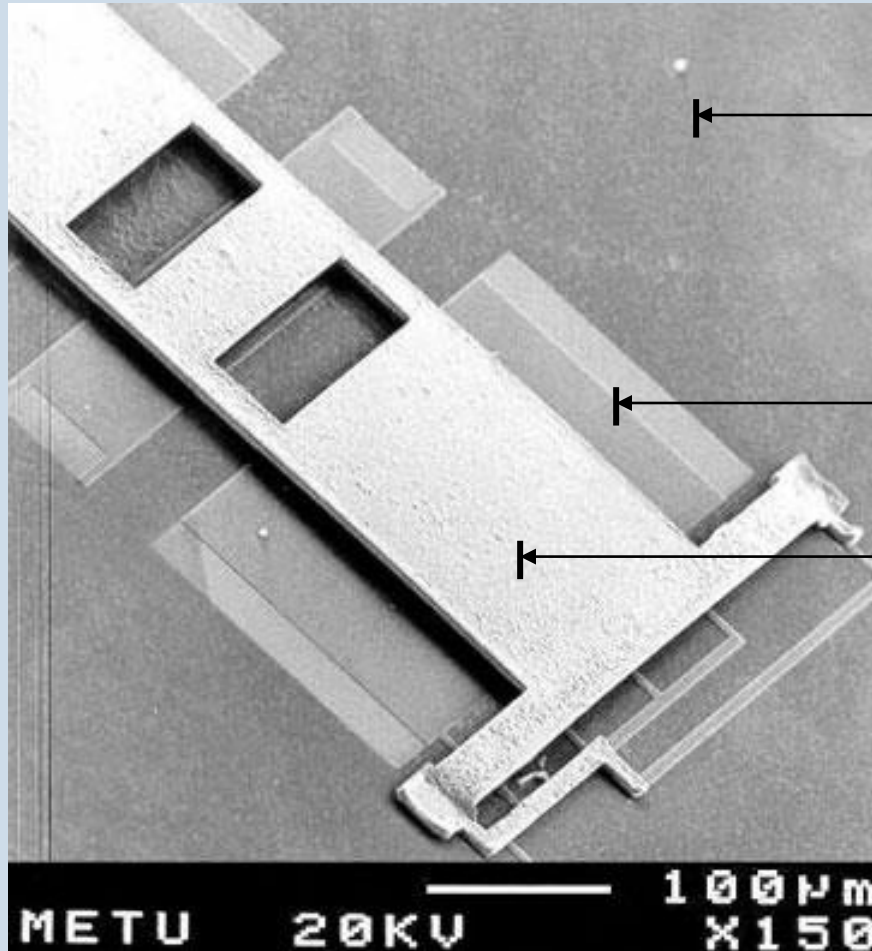
- Leg and motor linkage near the shuttle



University of California at Berkeley and Micropropulsion Corp. USA

Seth Hollar and Anita Flynn

RF MEMS Device



Substrate: Pyrex 7740 Glass

Base Metal: Sputtered AL

Suspended Metal Layer:
Electroplated Ni

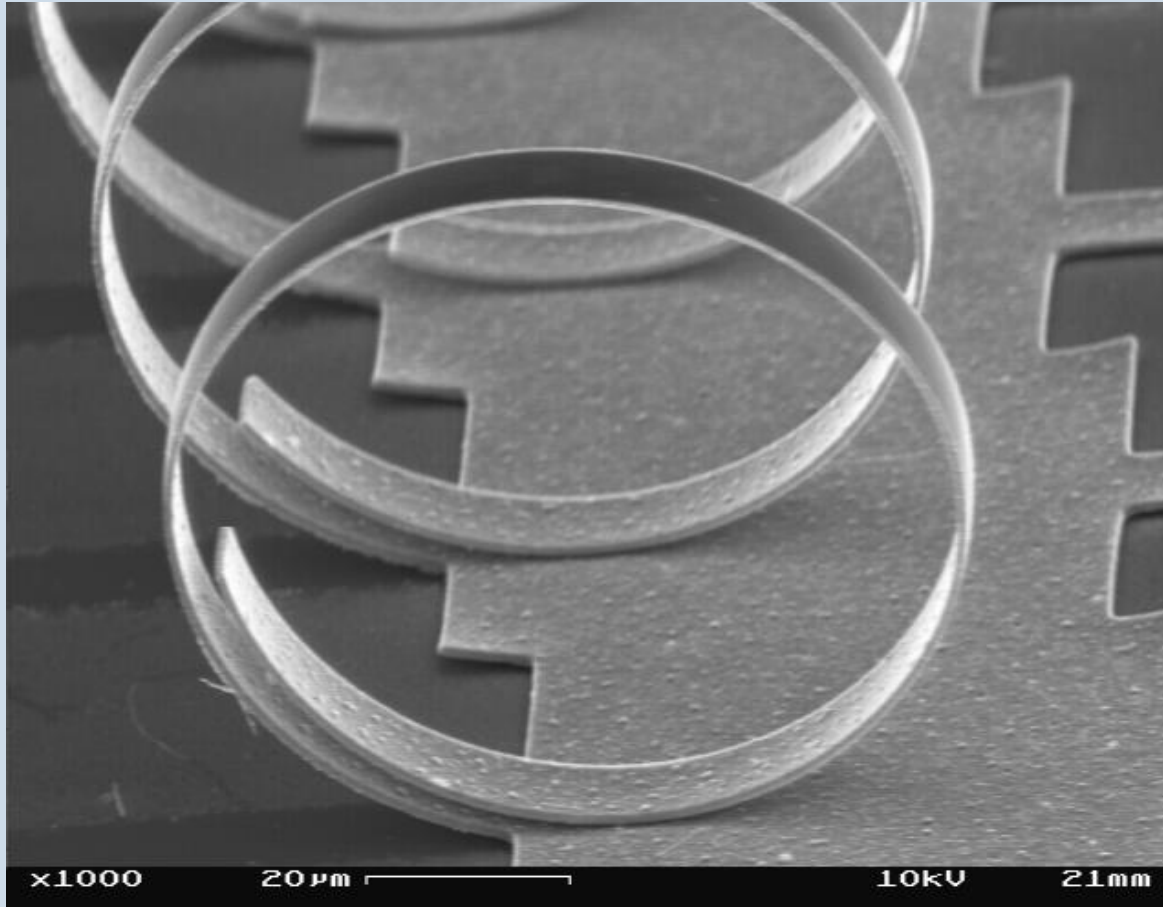
Sacrificial Layer: Photo Resist
Beam Length: 600µm
Gap Size: 5µm

RF MEMS Capacitive Switch



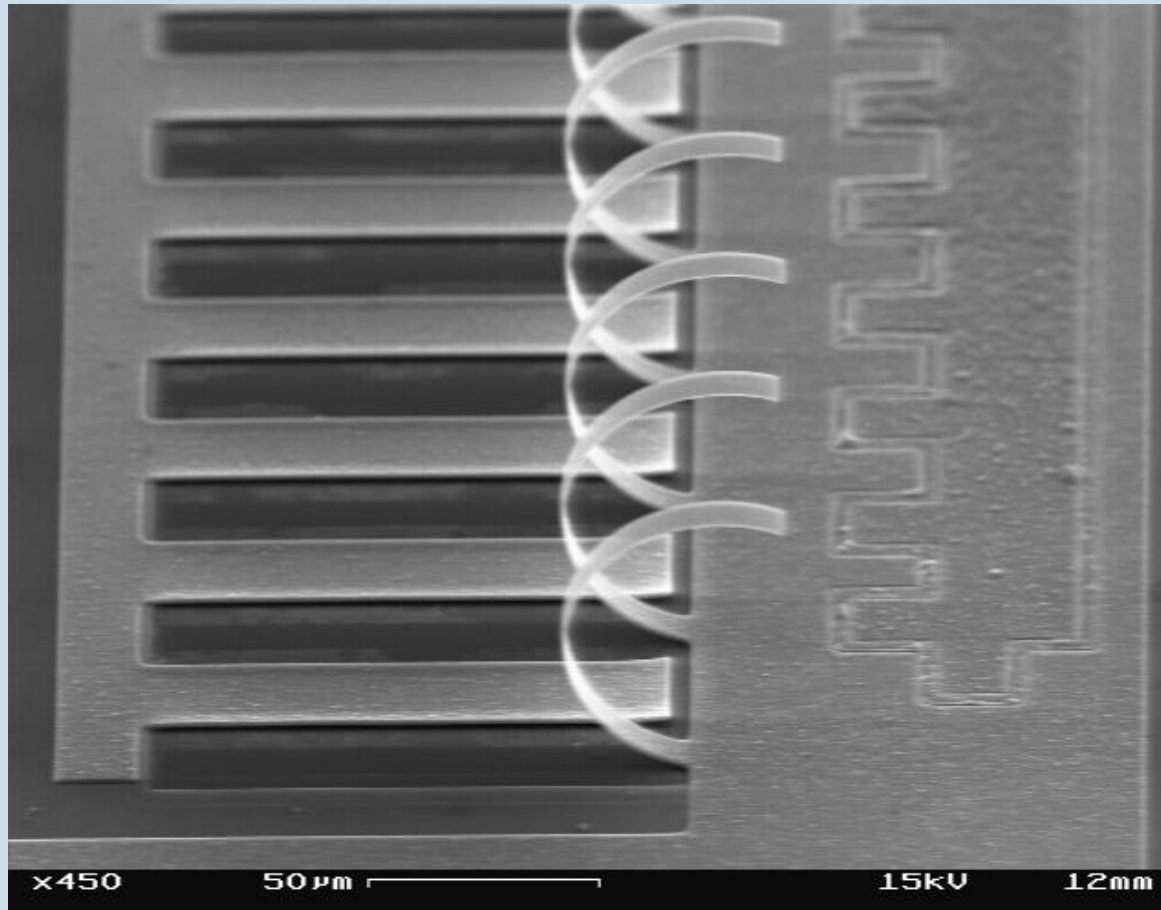
BEAM Length Vary Between $800\mu\text{m}$ - $1000\mu\text{m}$

Released Cantilevers post thermal annealing



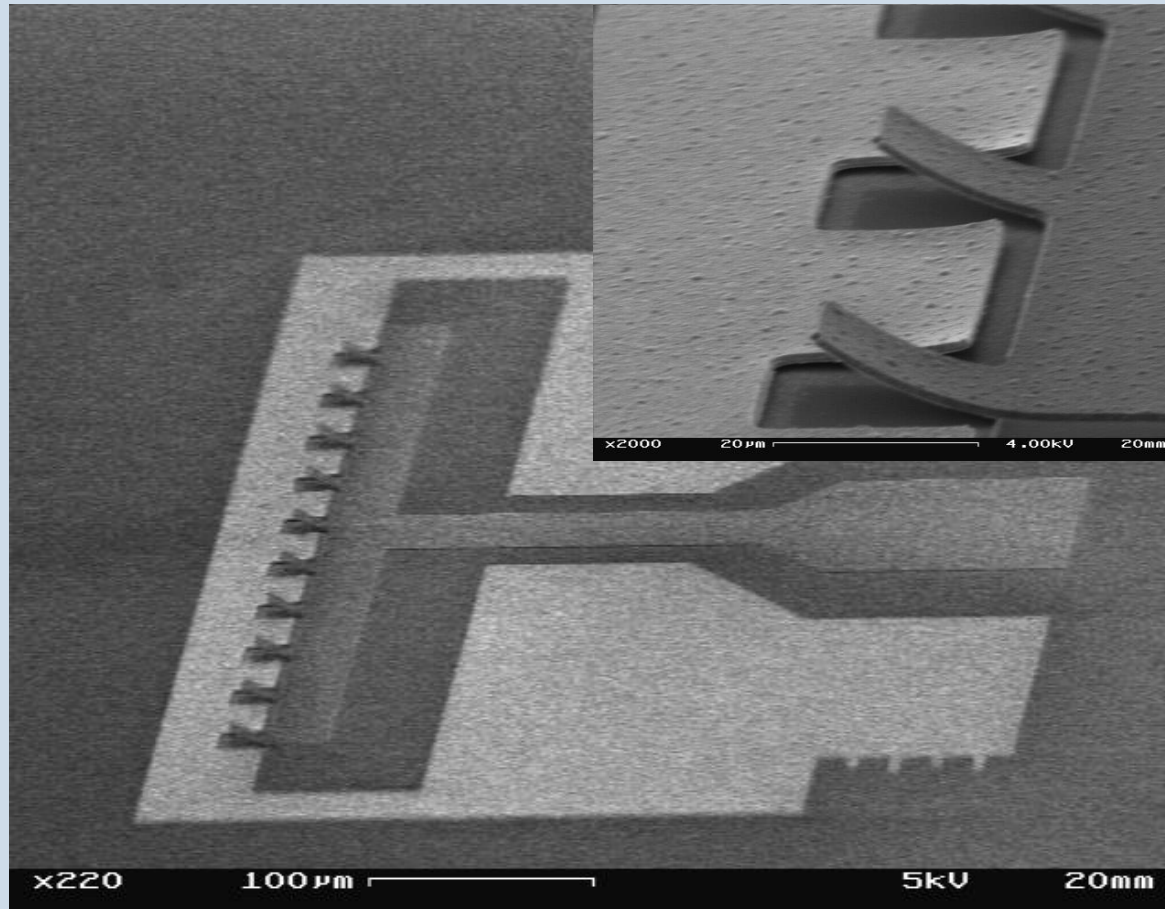
Université Catholique de Louvain, Belgium
Nicolas André

Thermal Actuated Actuators



Université Catholique de Louvain
Nicolas André

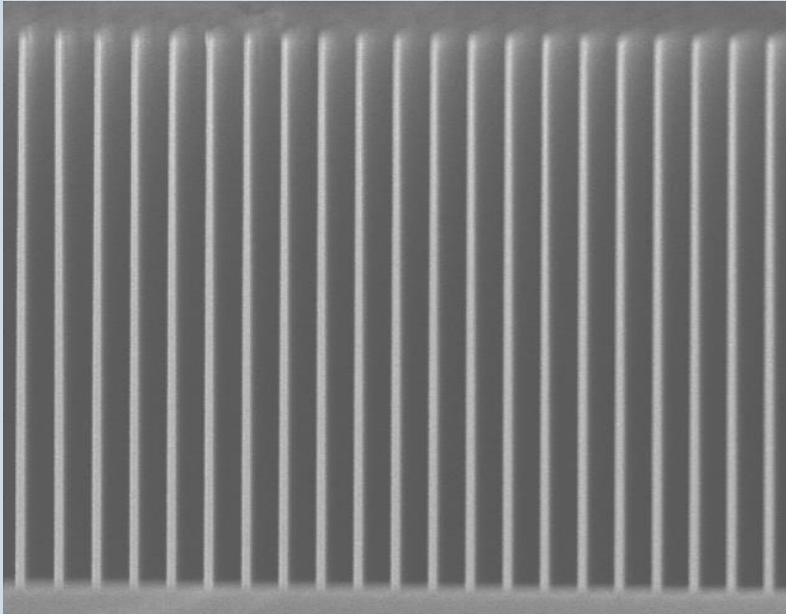
A flow sensor fabricated using the process flow



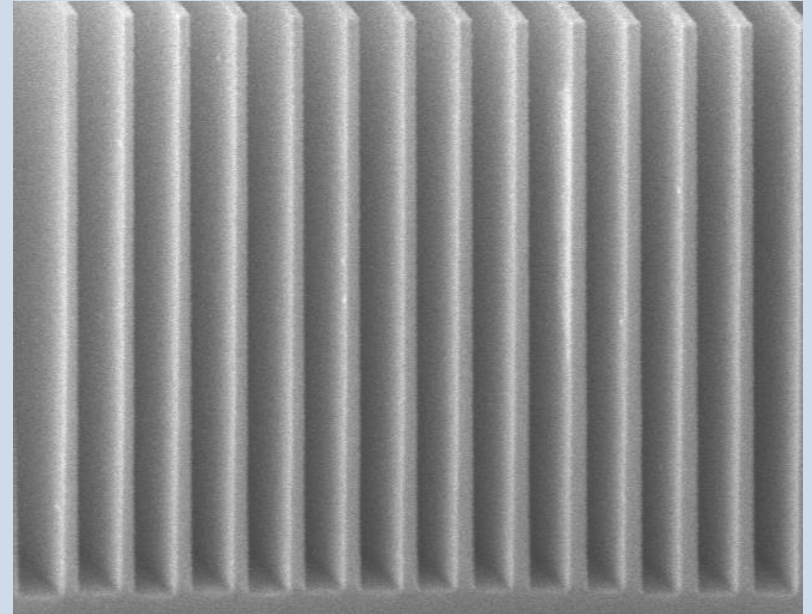
Université Catholique de Louvain
Nicolas André

High aspect ratio silicon gratings

Autosamdri[®]-815B, Series B Processed



SEM: 5kV, 10,000x
Pitch: 574 nm, Height: 8 μm, Depth 40 μm
Aspect ratio: ~ 100

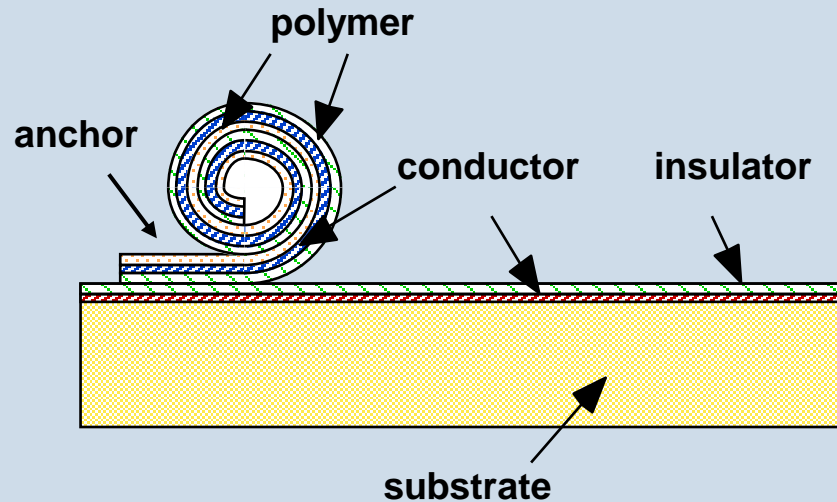


SEM: 5kV, 40,000x
Pitch: 200 nm, Height: 2.5 μm, Depth: 20 μm
Aspect ratio: ~ 50

Massachusetts Institute of Technology
Minseung Ahn

ARTIFICIAL EYELID ACTUATOR

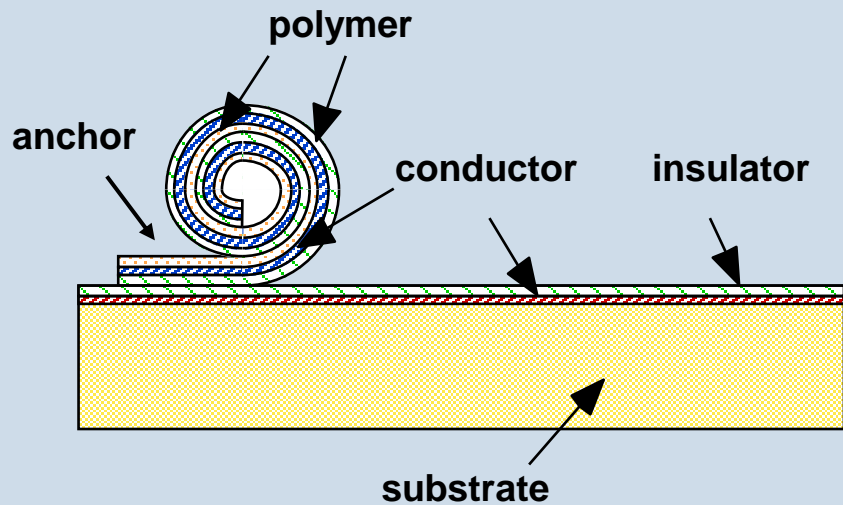
- Flexible film electrostatic actuator-



- ***Polymer/metal thin film stack is fabricated and released from the substrate***
- ***Thermal and mechanical stress causes curling of the actuator when released***
- ***Electrostatic force uncurls film; recoils when voltage removed***
- ***Large electrostatic displacement, high operating frequency (>1 kHz)***

ARTIFICIAL EYELID ACTUATOR

- Flexible film electrostatic actuator



Potential Applications

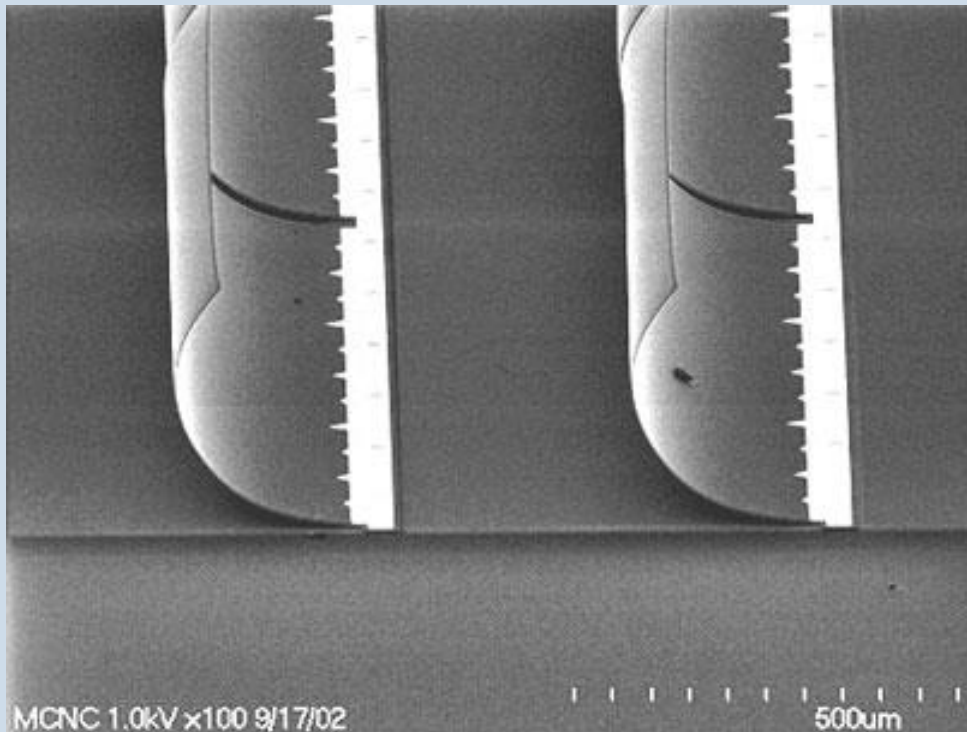
- *Optical Shutters*
- *Electrical Relays*
- *Microvalves*

MCNC Research & Development Institute, USA

David Dausch, PhD

ARTIFICIAL EYELID ACTUATOR

- Arrays of 500 μ m width actuators; curl is tailored based on thicknesses of layers

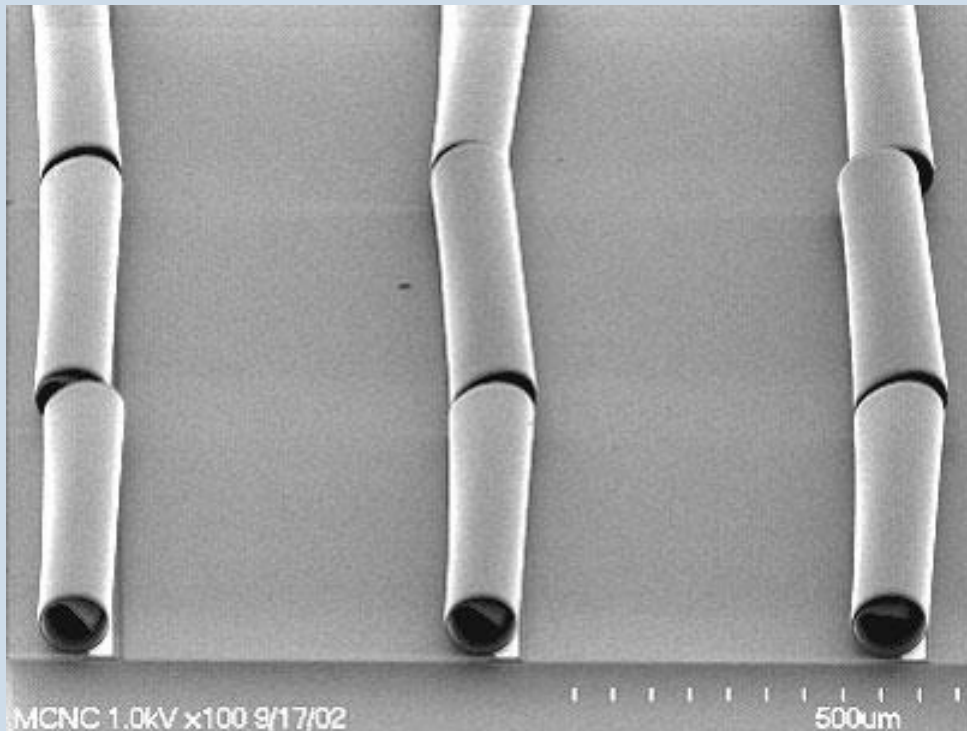


Large curl devices

- 800nm Au film in flexible electrode
- 120° curl, 250 μ m radius
- 50-90V operating voltage
- 40% open area

ARTIFICIAL EYELID ACTUATOR

- Arrays of 500 μ m width actuators; curl is tailored based on thicknesses of layers



Tight curl devices

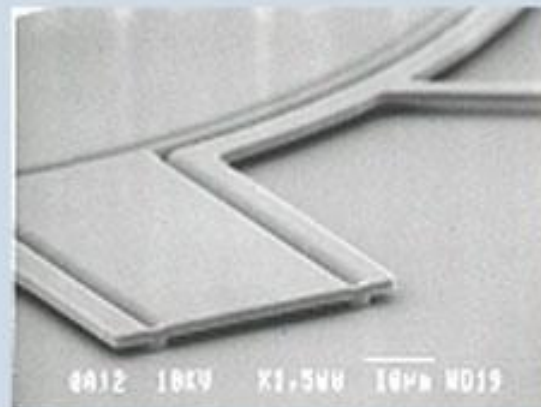
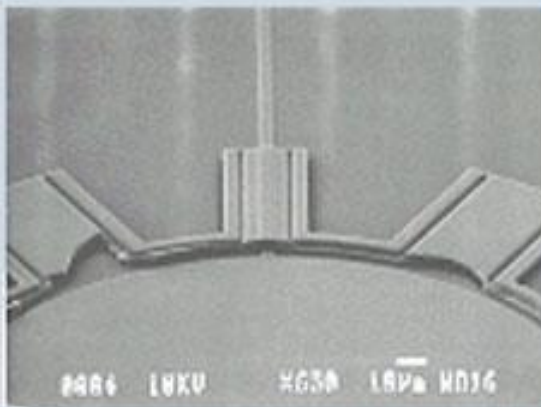
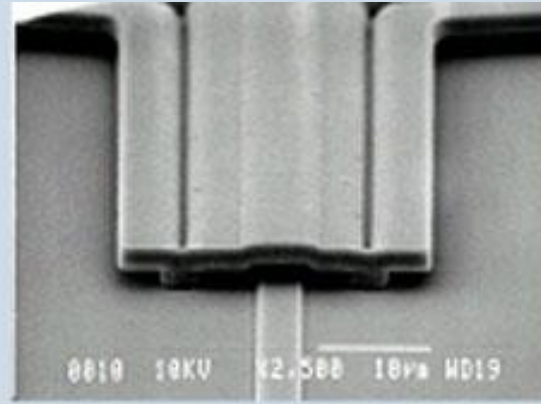
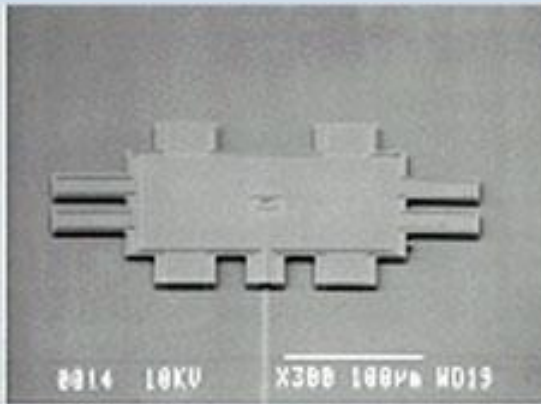
- 50nm Au film in flexible electrode

- 640° curl, 45 μ m radius

- 220-340V operating voltage

- 80% open area

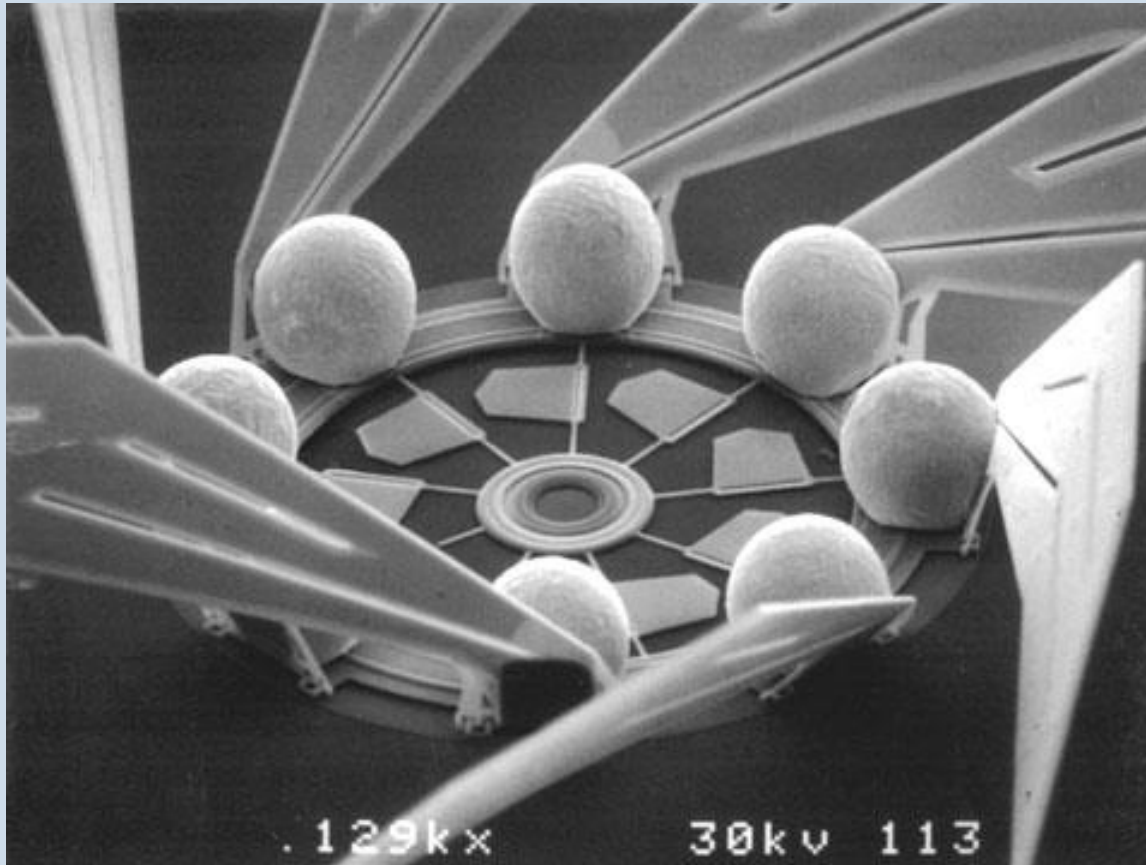
MEMSJet Drop Ejector



XEROX CORPORATION, USA

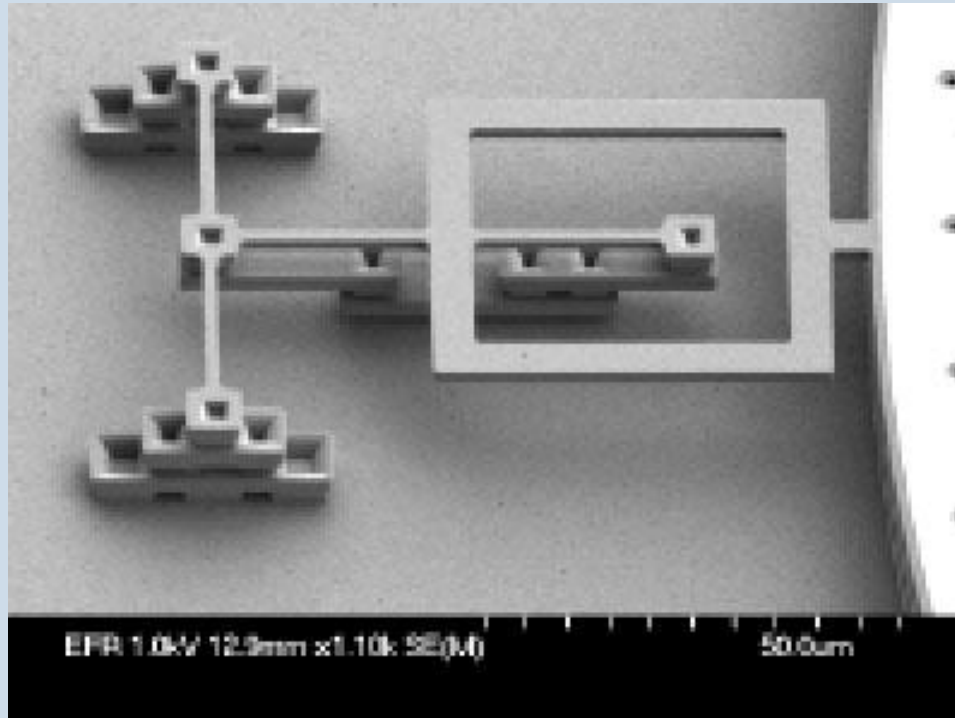
Joel A. Kubby

Solderfan



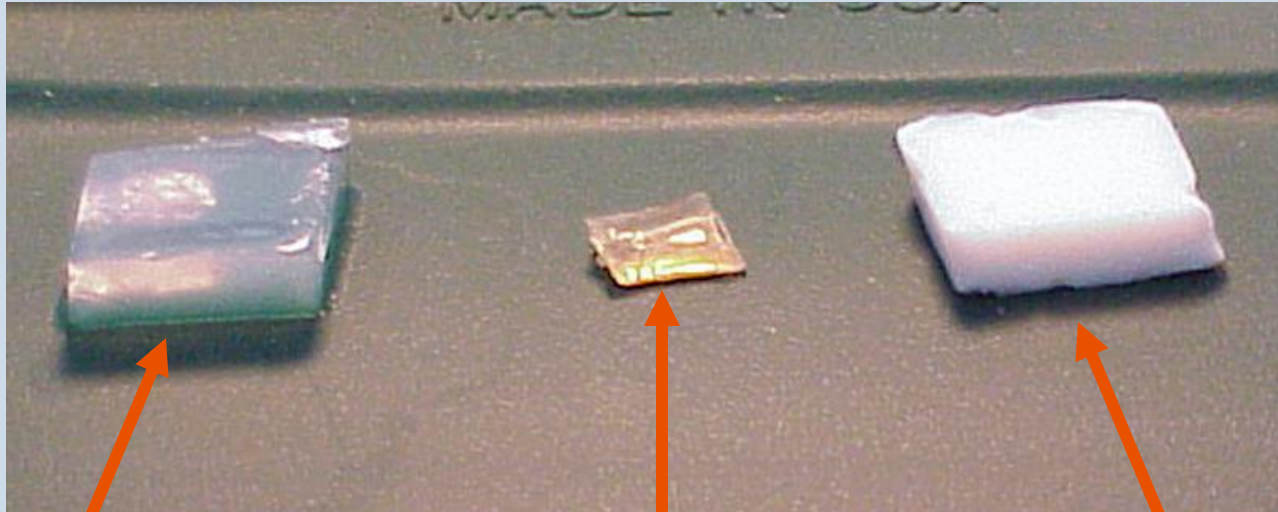
ETH, Switzerland
Ryan Linderman

Unique MEMS Hinge



MEMX
New Mexico, USA

SAMDRIED™ vs. AIRDRIED Sol-Gel



SOL-GEL
0.1% solids in H₂O
Alcohol Dehydration

SAMDRIED™

SOL-GEL
1.0% solids in H₂O
Alcohol Dehydration

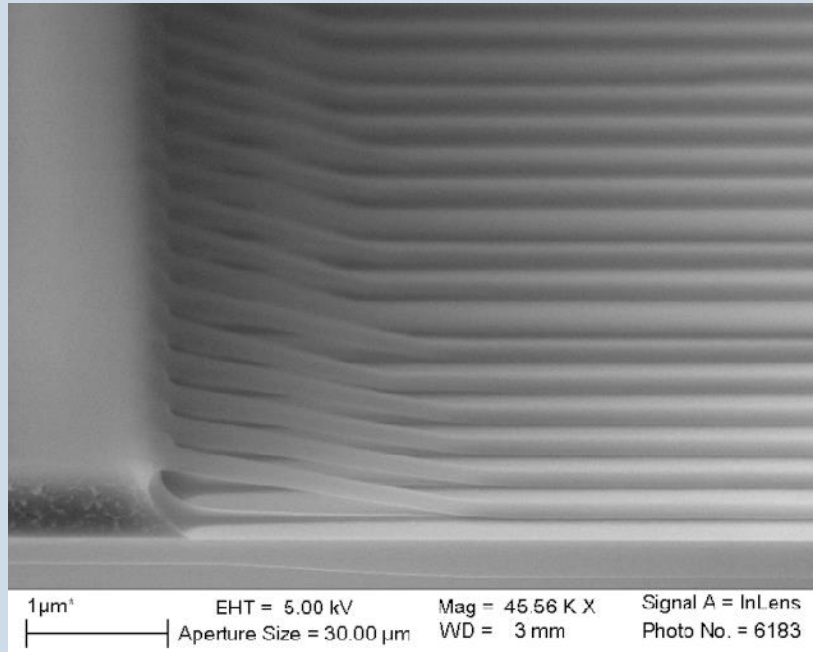
AIRDRIED

SOL-GEL
1.0% solids in H₂O
Alcohol Dehydration

SAMDRIED™

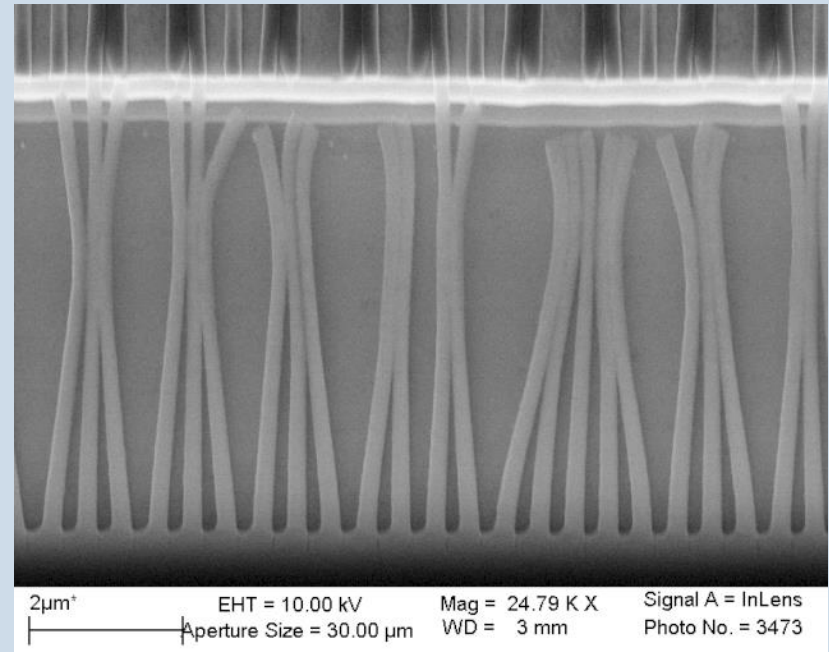
Tousimis Research Corporation
Rockville, MD

Failed attempts to get thick (~200 nm) and high repetitive (~ 500 nm) film

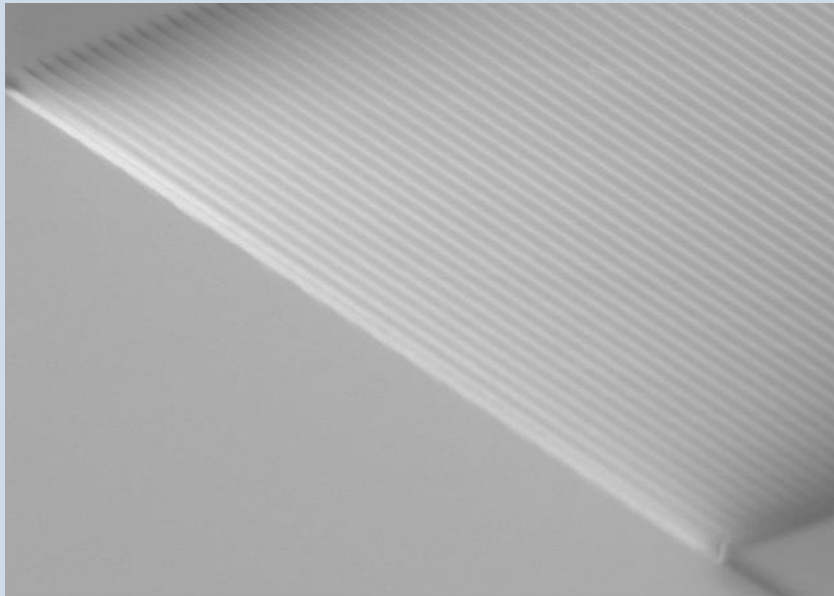


① Bi-layer e-beam resist
- top resist pattern couldn't sustain and collapsed down.

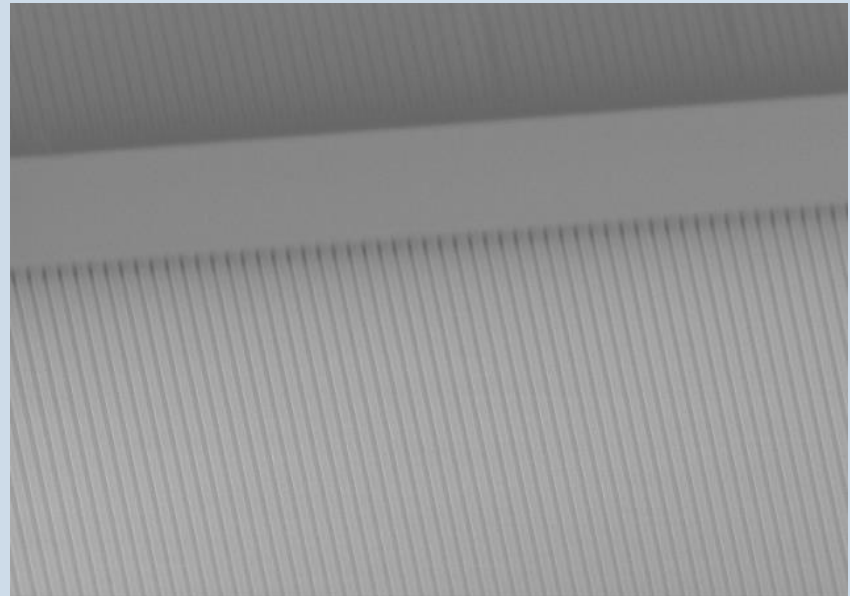
② Single thick e-beam resist
- Resist pattern collapsed each other during drying process.



E-beam resist pattern quality after CPD Process



3 μ m* EHT = 5.00 kV Mag = 14.12 K X Signal A = InLens
Aperture Size = 30.00 μ m WD = 4 mm Photo No. = 2967



3 μ m* EHT = 5.00 kV Mag = 10.77 K X Signal A = InLens
Aperture Size = 30.00 μ m WD = 4 mm Photo No. = 2972

The same repetitive pattern was fabricated using 450 nm thick e-beam resist. Patterned, developed, and transferred to IPA prior to CPD Process. Patterns are all coherent and no defects were found.

NRL Nano Fab - Washington, DC
Chul-Soo Kim